

Amendments to the Drawings:

The attached replacement sheets of drawings include changes to Figs. 1-3. These sheets replace all previous versions of the drawings, which include: the original sheets filed with the application, the replacement sheets filed on April 1, 2002, and the amended drawings filed on February 28, 2003 along with a previous response.

In Figure 1, the lead line for reference numeral 18 has been corrected to correspond with the originally filed drawings, the outline for nitride layer 40 has been added to correspond with the originally filed drawings, and the term “related art” has been replaced with “prior art” as previously requested by the Office.

In Figure 2, the outline for region 50 has been added to correspond with the originally filed drawings, the lead lines for reference numerals 50 and 26 have been corrected to correspond with the originally filed drawings, and the term “related art” has been replaced with “prior art” as previously requested by the Office.

In Figure 3, the lead lines for reference numerals 126, 128, and 130 have been corrected to correspond to the originally filed drawings.

Attachments: 3 Replacement Sheets

3 Marked Up Sheets Showing Changes



INVENTOR: MARK SIMPSON ET AL

Attorney Docket: US 010610

Title: DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE AND METHOD FOR FORMING THE SAME

Contact: STEVEN R. BIREN 914) 333-9630

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Replacement Sheet

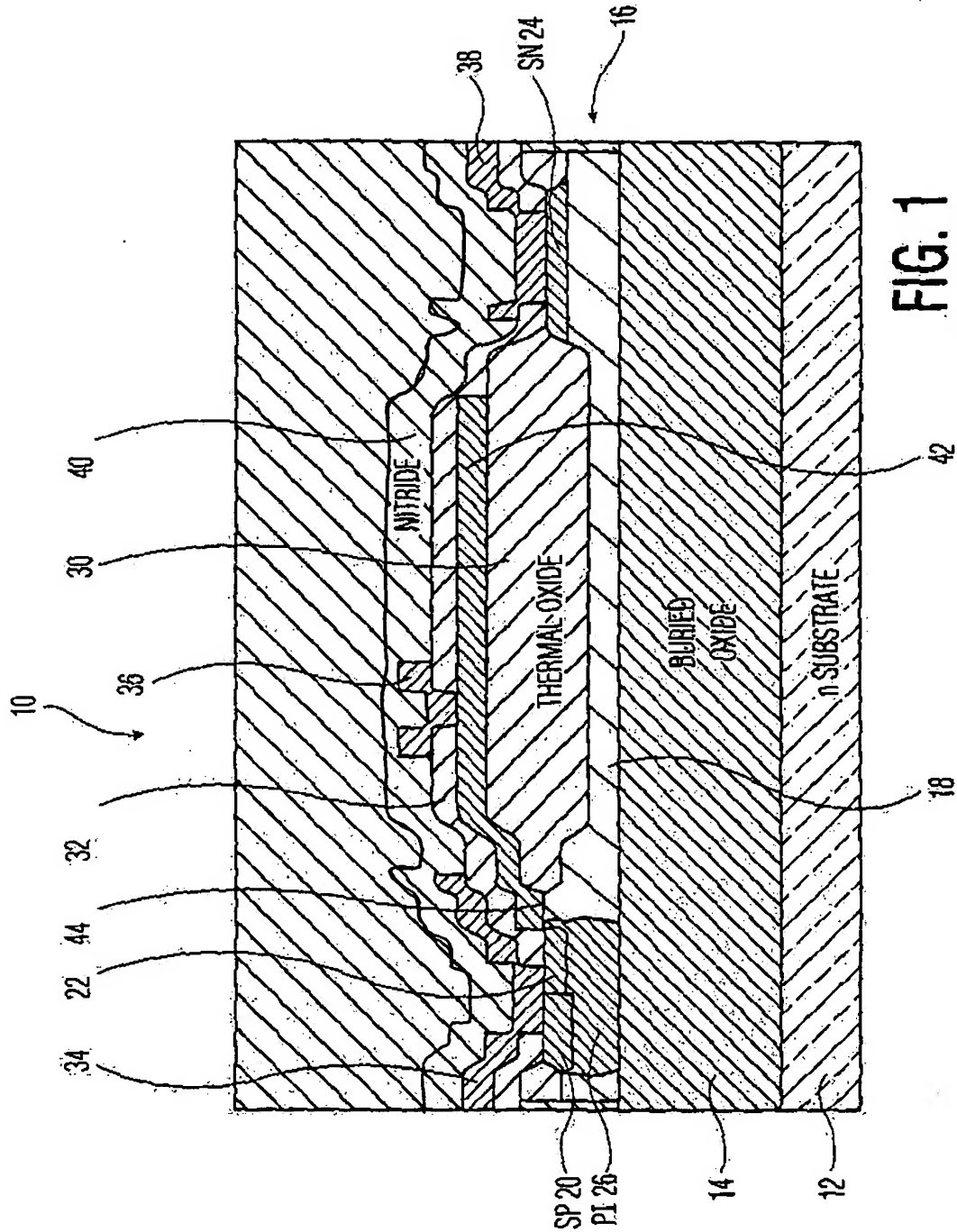


FIG. 1
PRIOR ART



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Replacement Sheet

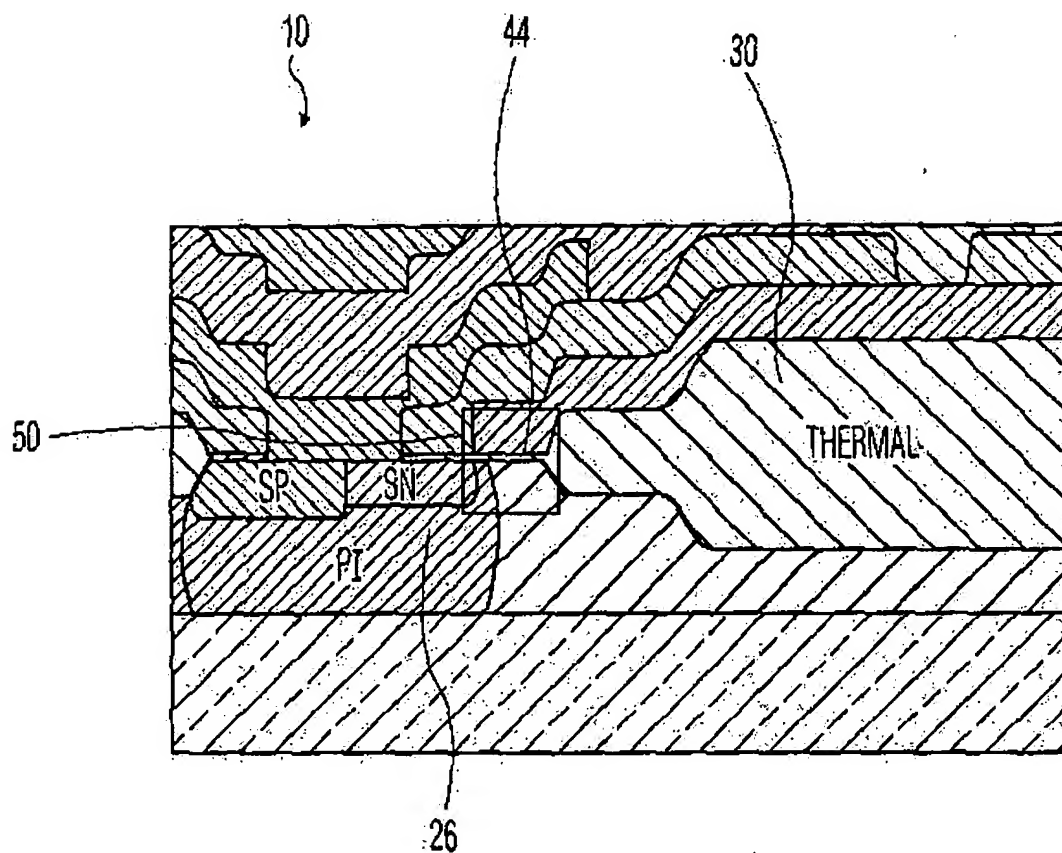


FIG. 2
PRIOR ART

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Replacement Sheet

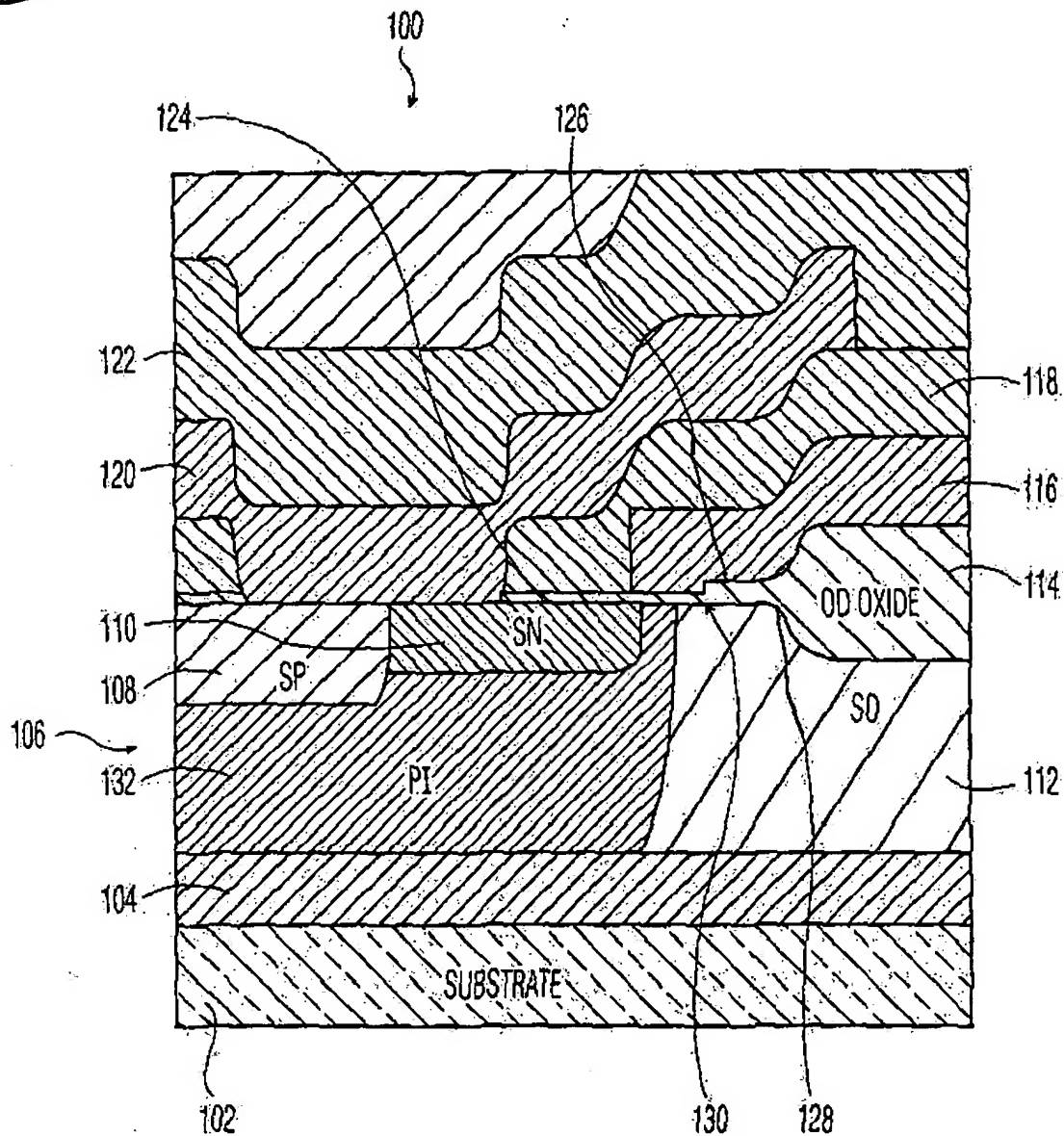


FIG. 3

INVENTOR: MARK SIMPSON ET AL

Attorney Docket: US 010610

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Replacement Sheet

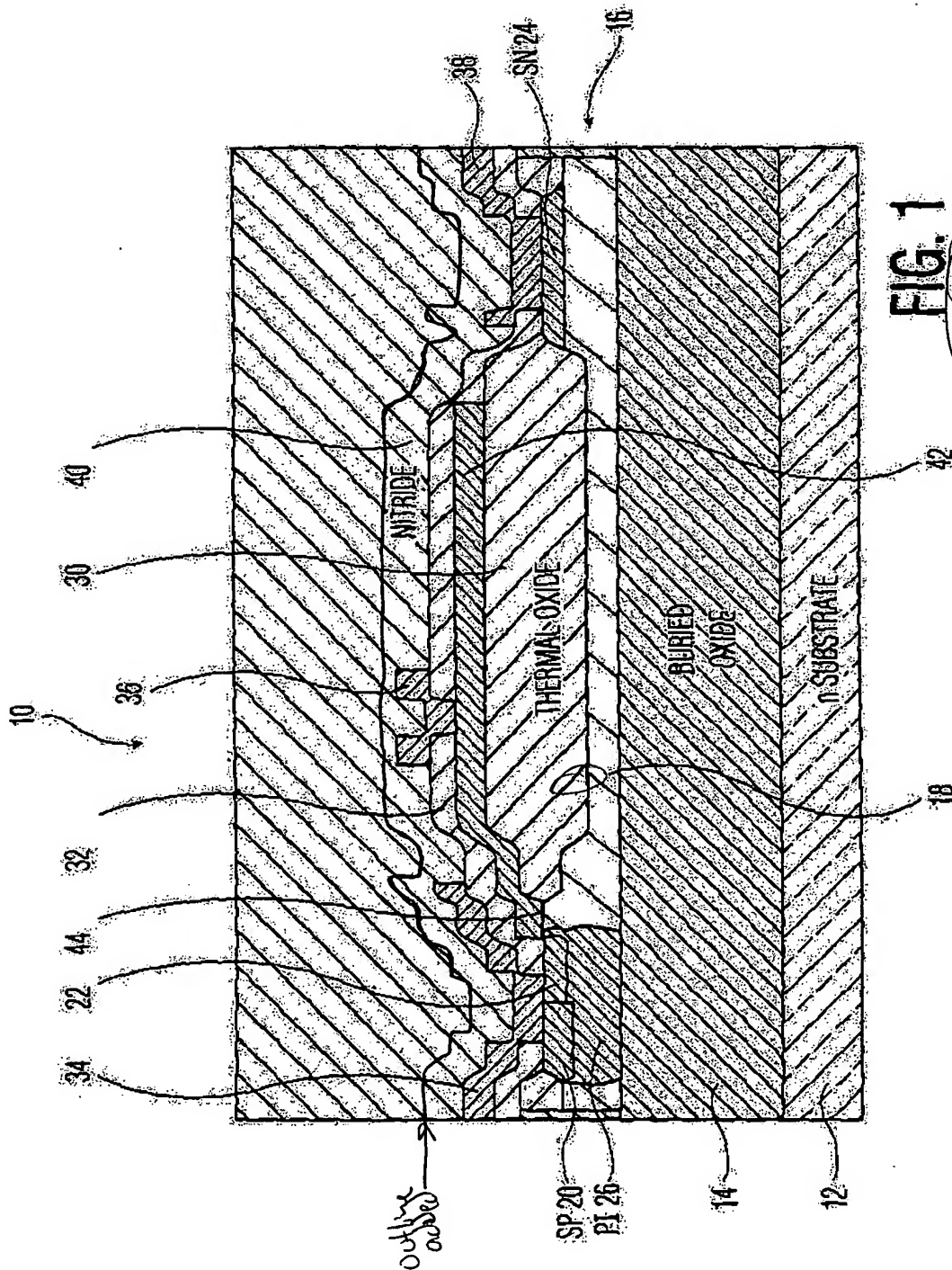


FIG. 1
PRIOR ART

was
"RELATED"

Lead Line
Corrected

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Markup Replacement Sheet

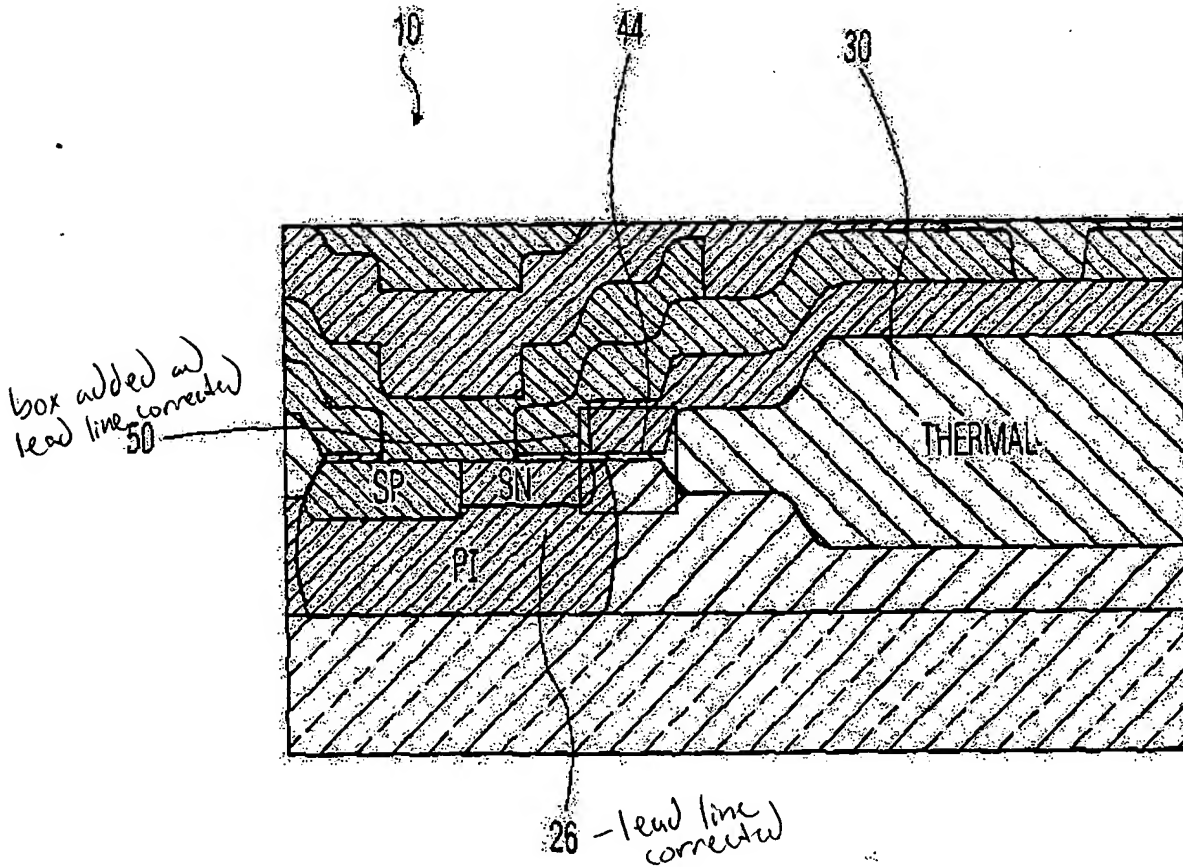


FIG. 2

PRIOR ART

was
"RELATED"

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Markup Replacement Sheet

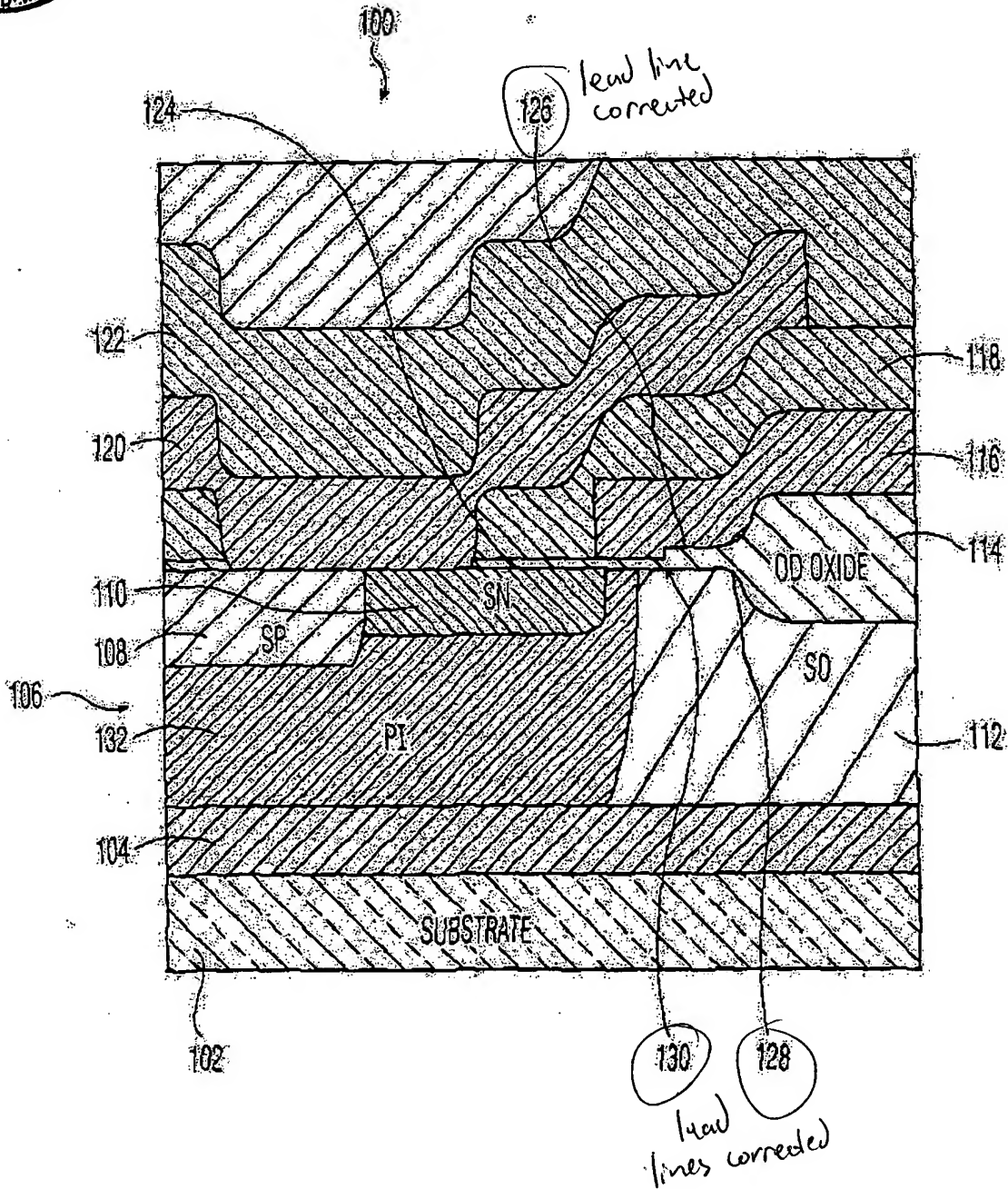


FIG. 3